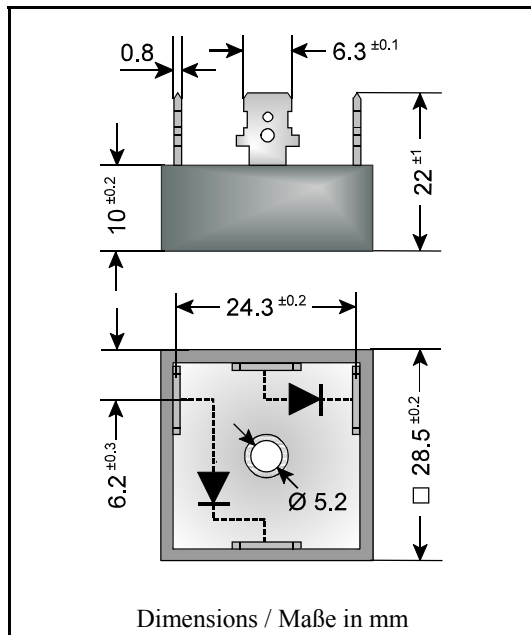


Silicon-Twin Rectifiers

Silizium-Doppeldioden



Nominal current Nennstrom	60 A
Alternating input voltage Eingangsschaltspannung	60...800 V
Plastic case with alu-bottom Kunststoffgehäuse mit Alu-Boden	
Dimensions Abmessungen	28.5 x 28.5 x 10 [mm]
Weight approx. Gewicht ca.	23 g
Compound has classification UL94V-0 Vergußmasse UL94V-0 klassifiziert	
Standard packaging: bulk Standard Lieferform: lose im Karton	see page 22 s. Seite 22



Recognized Product – Underwriters Laboratories Inc.® File E175067
Anerkanntes Produkt – Underwriters Laboratories Inc.® Nr. E175067

Maximum ratings

Grenzwerte

Type Typ	Repetitive peak reverse voltage Periodische Spitzenspannung V_{RRM} [V] ¹⁾	Surge peak reverse voltage Stoßspitzenspannung V_{RRM} [V] ¹⁾
D60 VC20	200	200
D60 VC40	400	400
D60 VC60	600	600
D60 VC80	800	800
D60 VC100	1000	1000
D60 VC120	1200	1200

Repetitive peak forward current Periodischer Spitzenstrom	$f > 15$ Hz	I_{FRM}	120 A ²⁾
Peak forward surge current, 50 Hz half sine-wave Stoßstrom für eine 50 Hz Sinus-Halbwellen	$T_A = 25^\circ\text{C}$	I_{FSM}	450 A
Rating for fusing – Grenzlasterintegral, $t < 10$ ms	$T_A = 25^\circ\text{C}$	i^2t	1000 A ² s
Isolation voltage – Isolationsspannung	$t = 1$ min	V_{ISO}	> 2000 V
Operating junction temperature – Sperrschichttemperatur		T_j	$-50...+150^\circ\text{C}$
Storage temperature – Lagerungstemperatur		T_s	$-50...+150^\circ\text{C}$

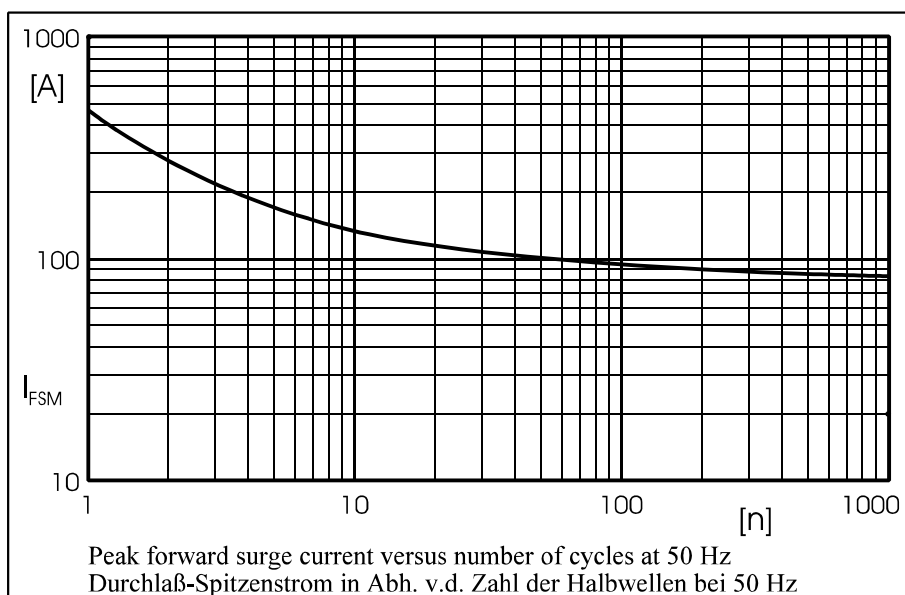
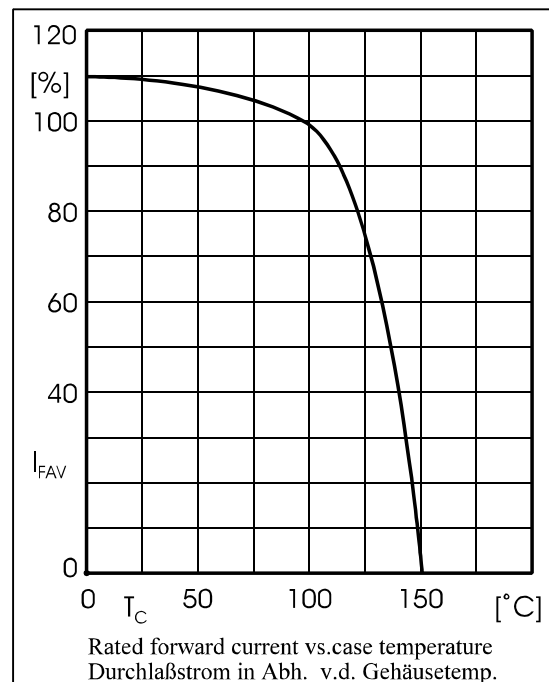
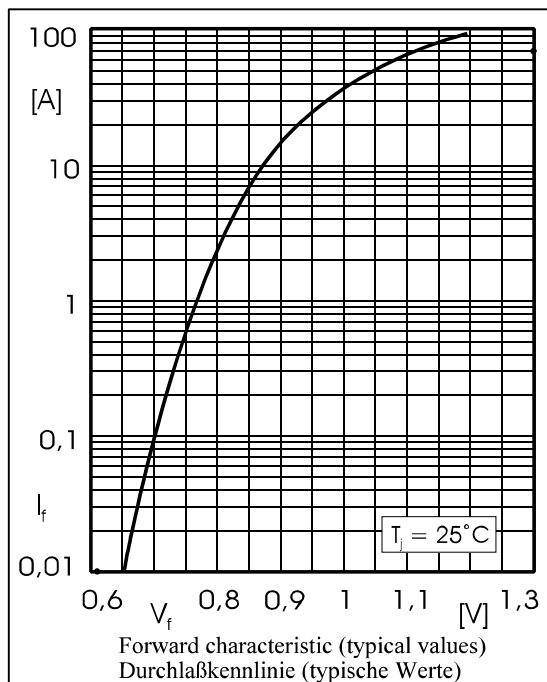
¹⁾ Valid per diode – Gültig pro Diode

²⁾ Max. case temperature $T_C = 100^\circ\text{C}$ – Max. Gehäusetemperatur $T_C = 100^\circ\text{C}$

Characteristics

Kennwerte

Forward voltage – Durchlaßspannung	$T_j = 25^\circ\text{C}$	$I_F = 60\text{ A}$	V_F	$< 1.1\text{ V}^1)$
Leakage current – Sperrstrom	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$	I_R	$< 100\text{ }\mu\text{A}$
Thermal resistance junction to case Wärmewiderstand Sperrschicht – Gehäuse			R_{thC}	$< 0.6\text{ K/W}$
Admissible torque for mounting Zulässiges Anzugsdrehmoment		10-32 UNF M 5		$18 \pm 10\%\text{ lb.in.}$ $2 \pm 10\%\text{ Nm}$



¹⁾ Valid per diode – Gültig pro Diode